

Fig.1

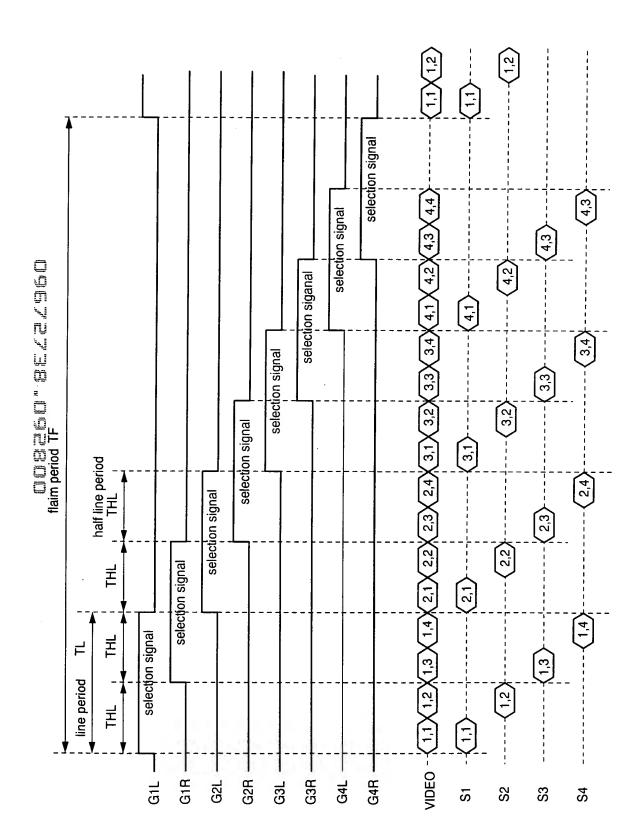


Fig.2

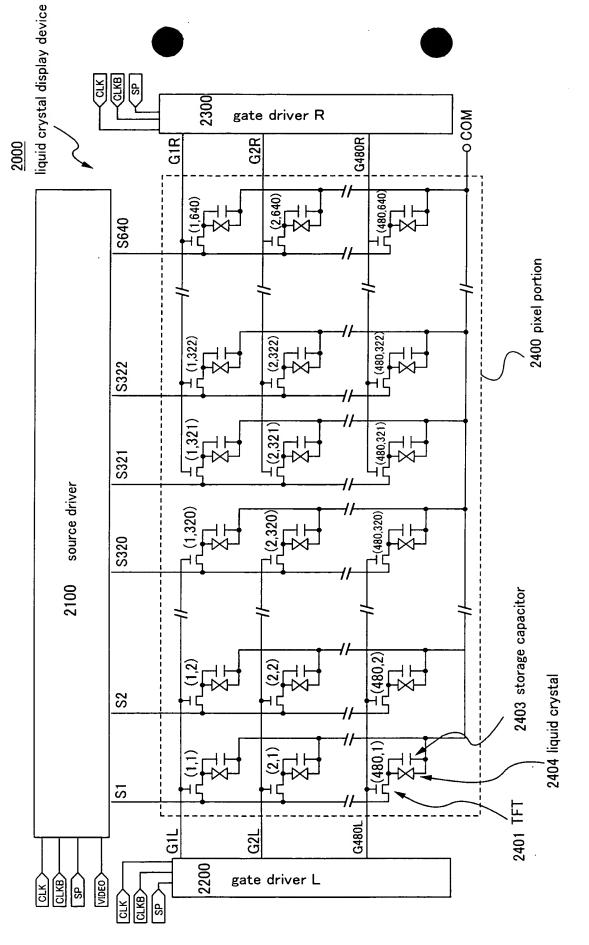


Fig.3

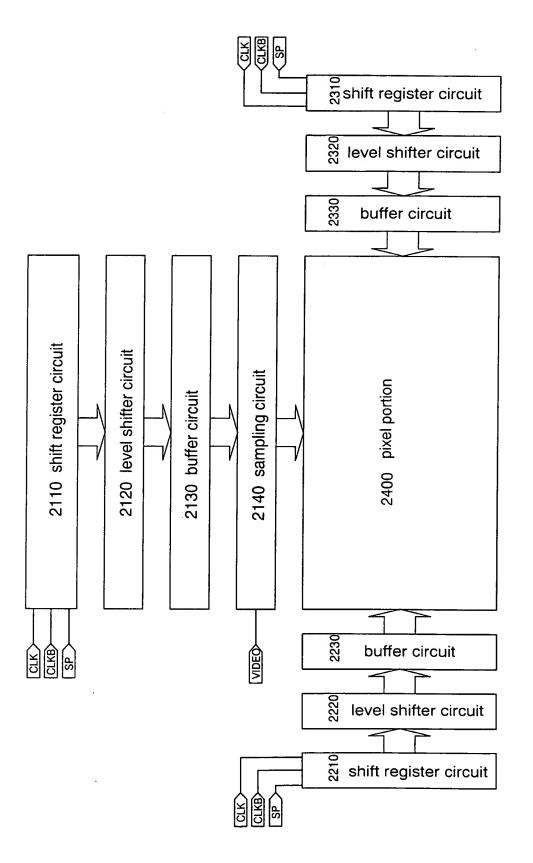


Fig.4

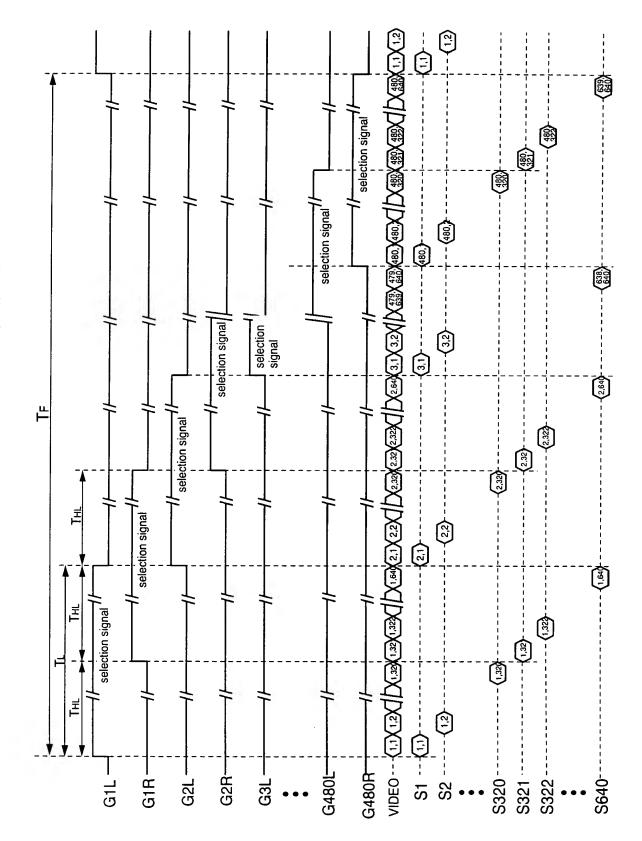


Fig.5

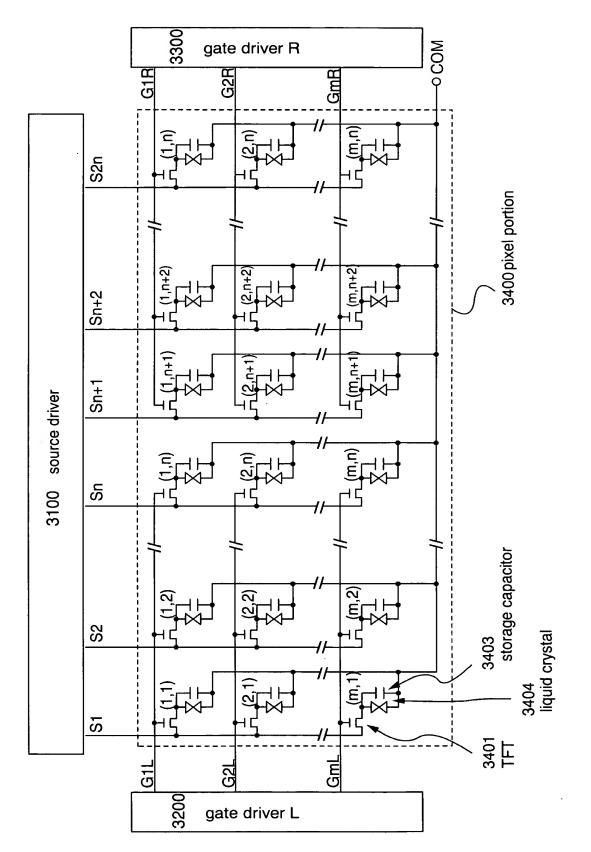


Fig.6

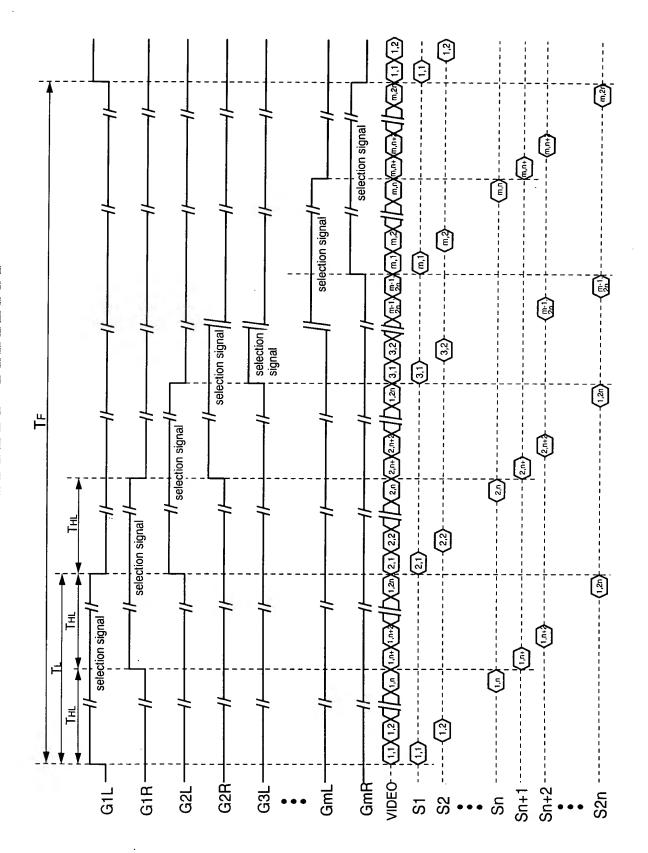
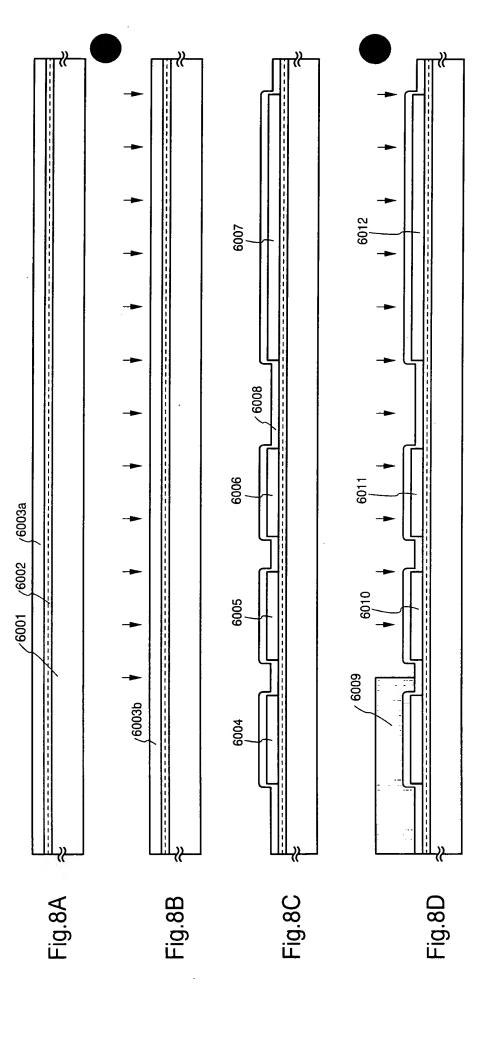
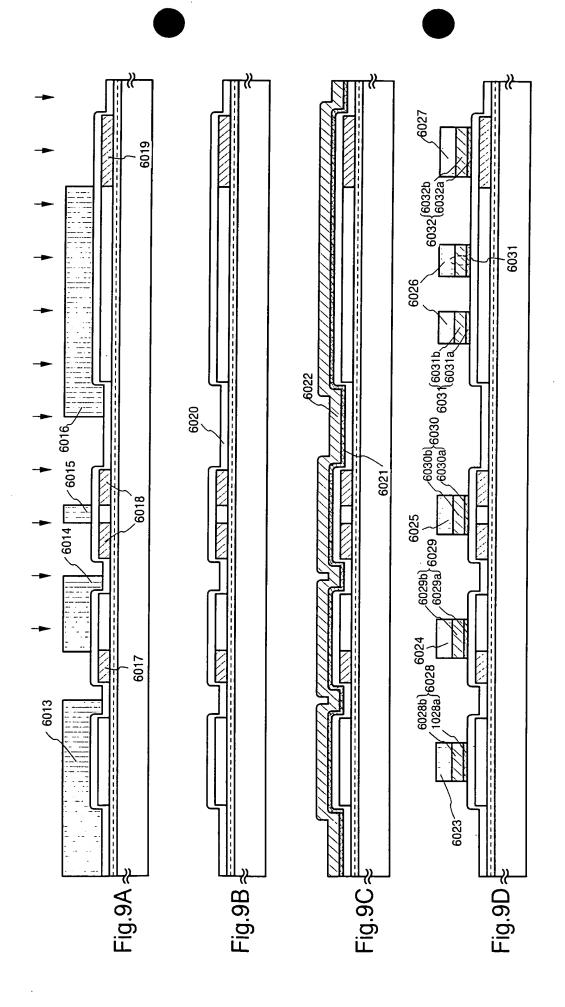
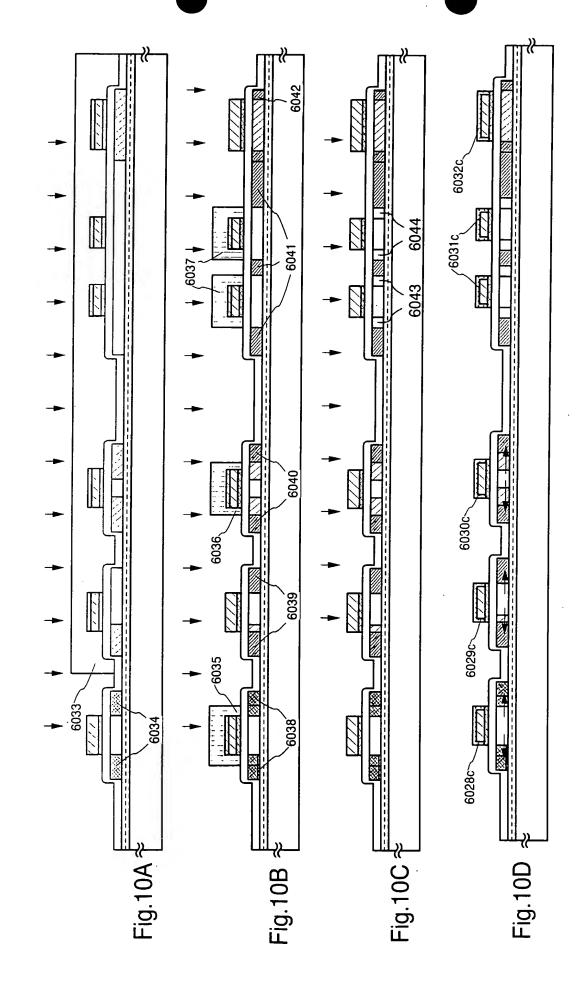
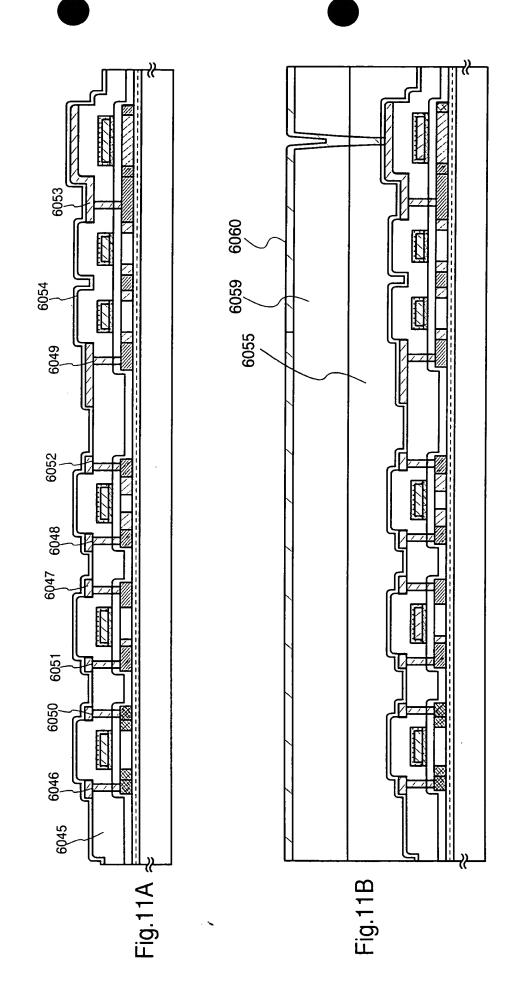


Fig.7









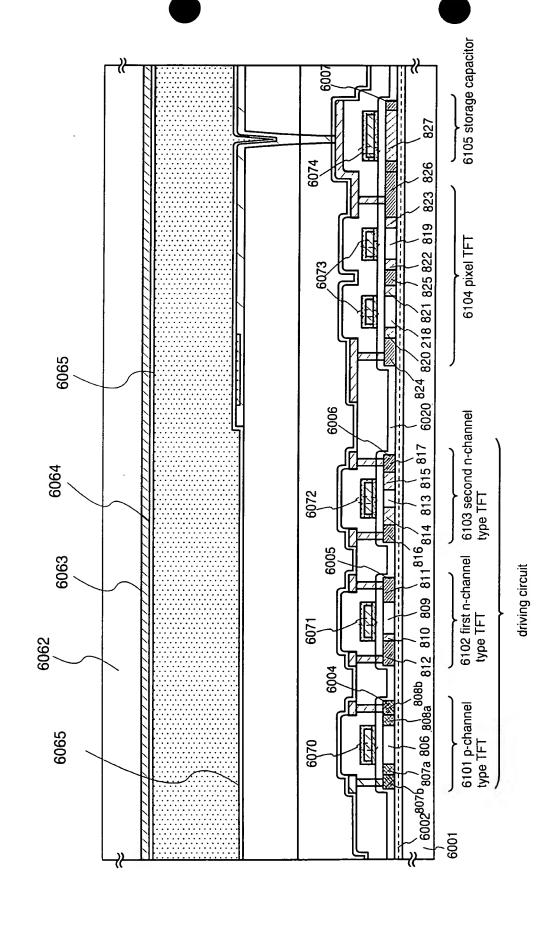
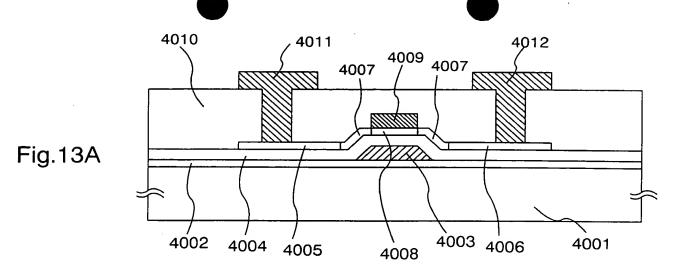


Fig.12



4001 substrate

4007 low concentration imprity region(LDD region)

4002 silicon oxide film

4008 channel forming region

4003 gate electrode

4009 channel protective film

4004 gate insulating film 4010 interlayer insulating film

4005 source region

4011 source electrode

4006 drain region

4012 drain electrode

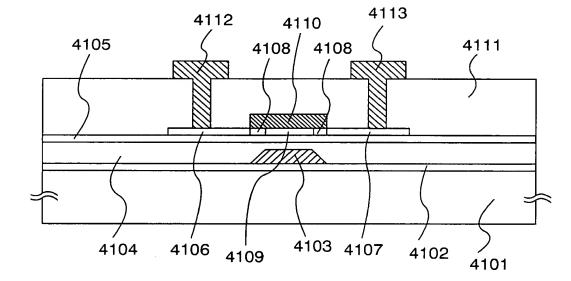


Fig.13B

4101 substrate

4108 low concentration impurity region(LDD region)

4102 silicon oxide film

4109 channel forming region

4103 gate electrode

4110 channel protecting film

4104 bezocyclobutene(BCB) 4111 interlayer insulating film

4105 silicon nitride film

4112 source electrode

4106 source region

4113 drain electrode

4107 drain region

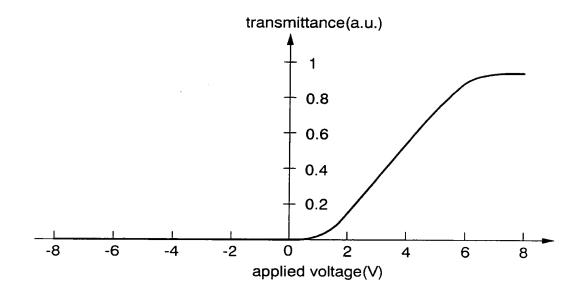
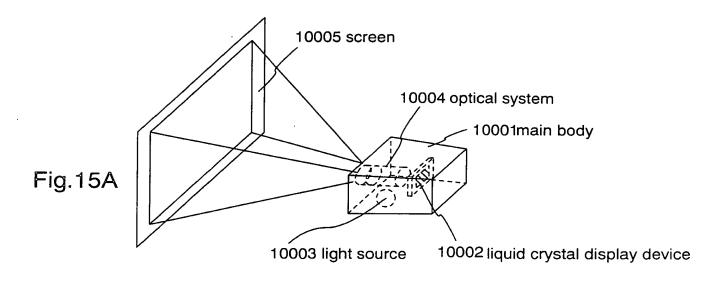
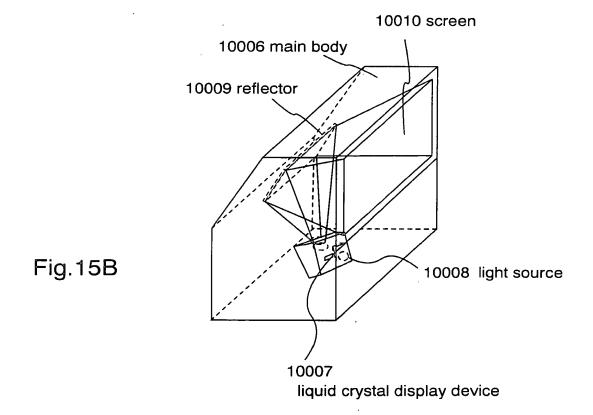
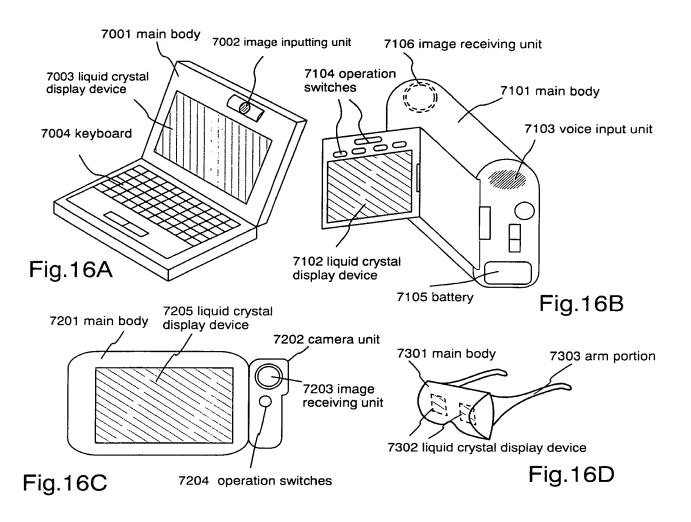


Fig.14







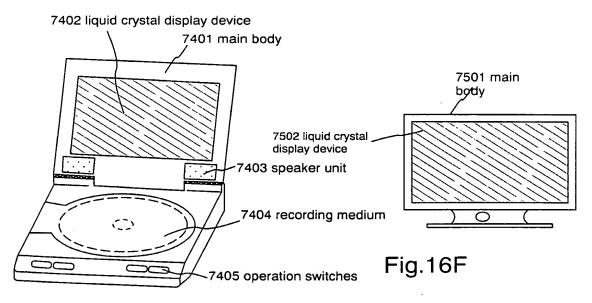


Fig.16E

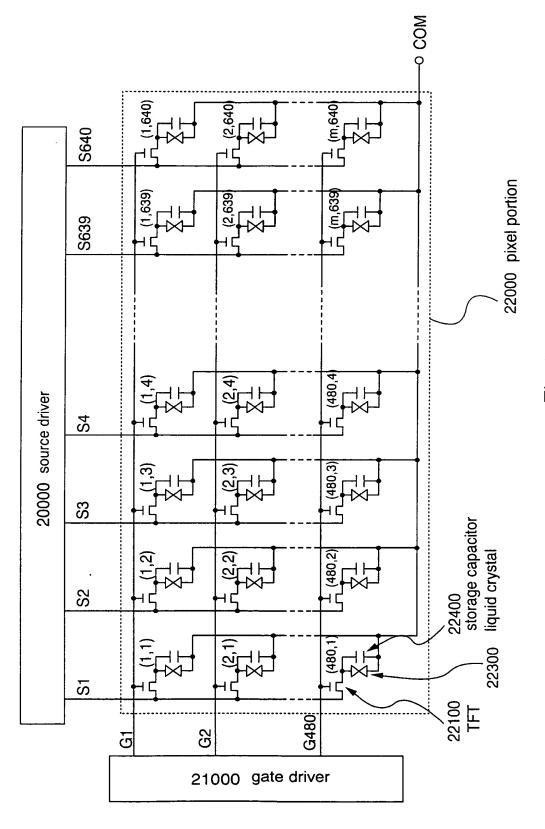


Fig.17

Fig.18

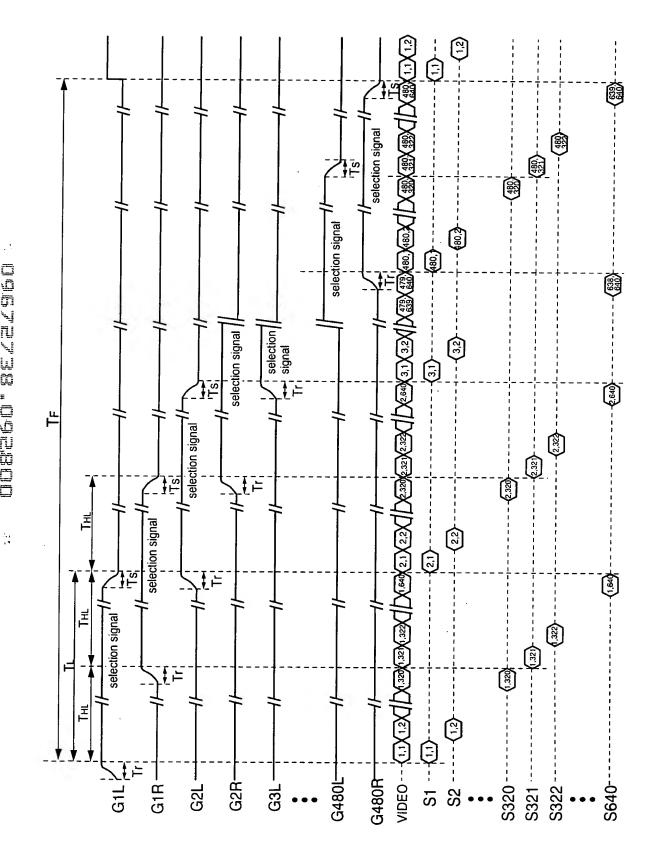


Fig.19